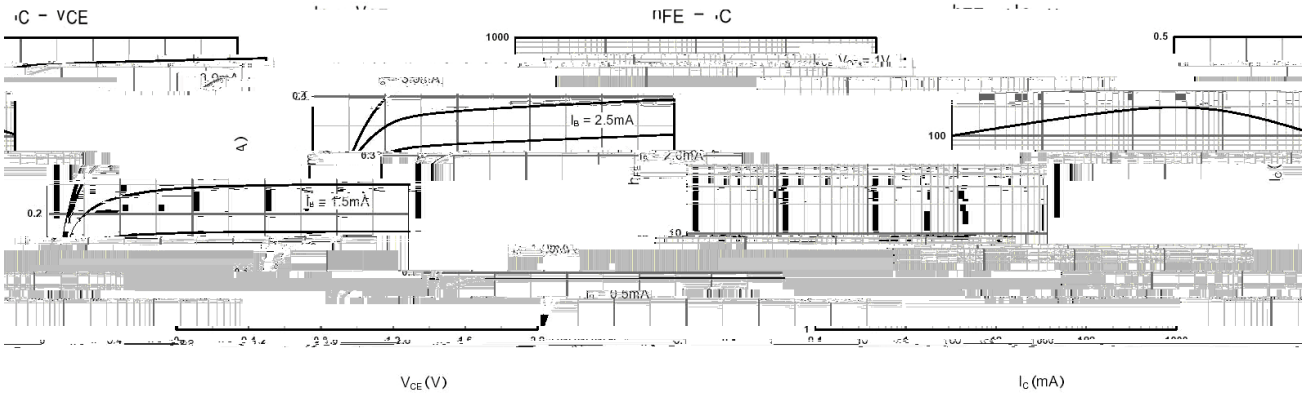
/ Absolute Maximum Ratings(Ta=25)

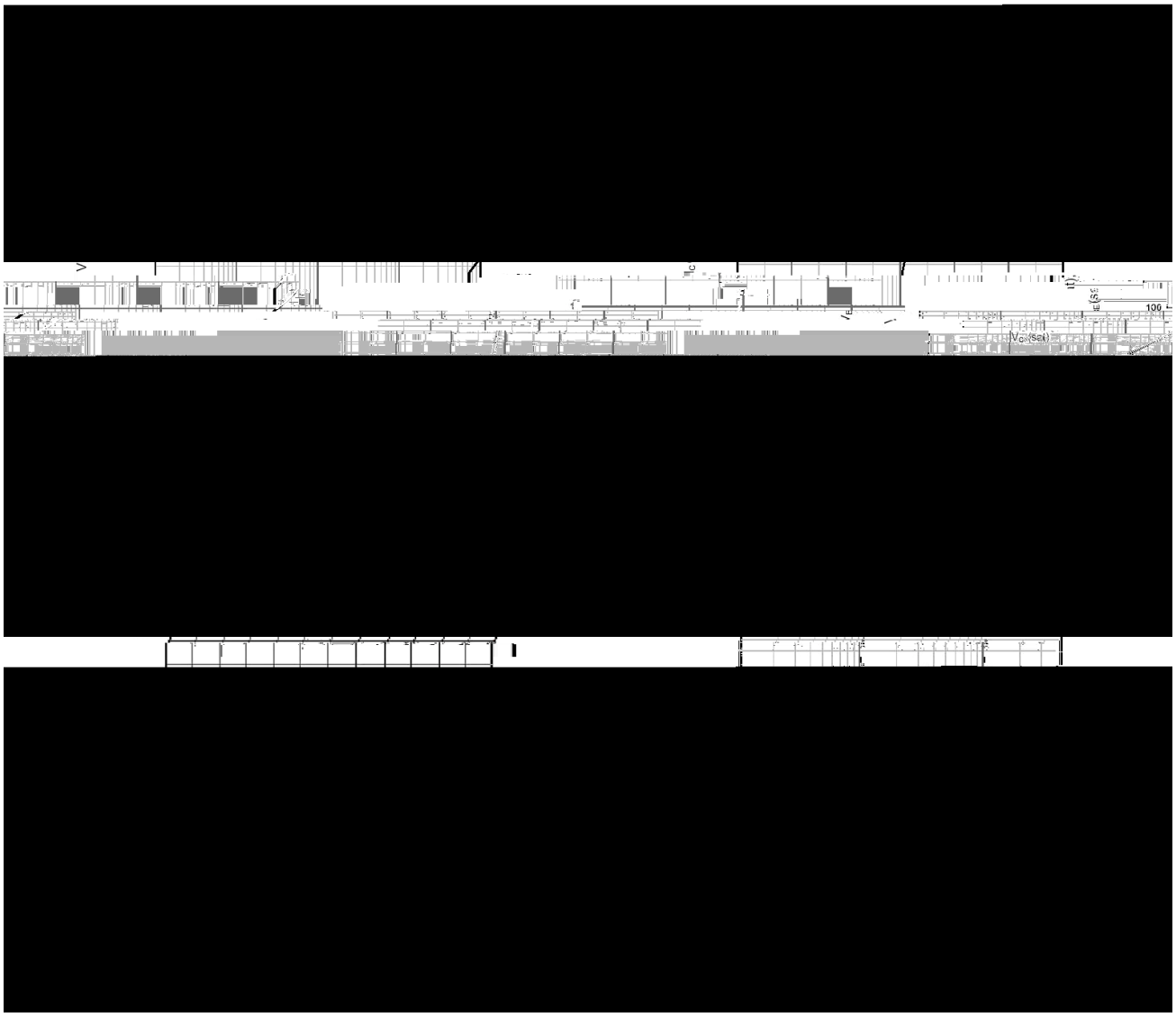
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-800	mA
Base Current - Continuous	I_B	-200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

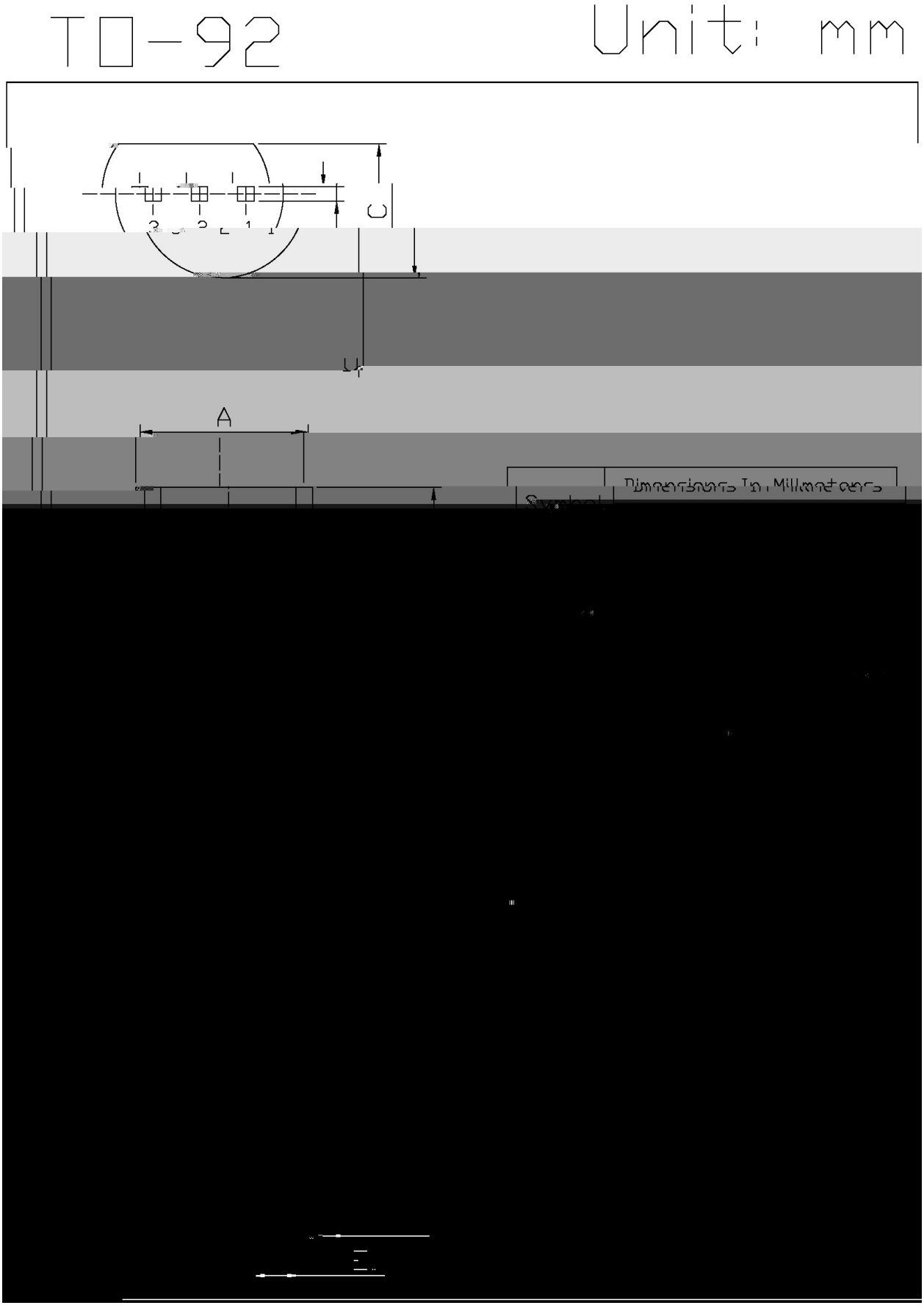
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-2.0mA I_B=0	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	85		300	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-500mA	40			
	$h_{FE(3)}$	V_{CE}=-1.0V I_C=-5.0mA	45			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA I_B=-50mA		-0.28	-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-500mA I_B=-50mA		-0.98	-1.2	V
Base to Emitter Voltage	V_{BE}	V_{CE}=-1.0V I_C=-10mA		-0.66	-1.0	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-50mA	100	200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		15		pF

/ Electrical Characteristic Curve

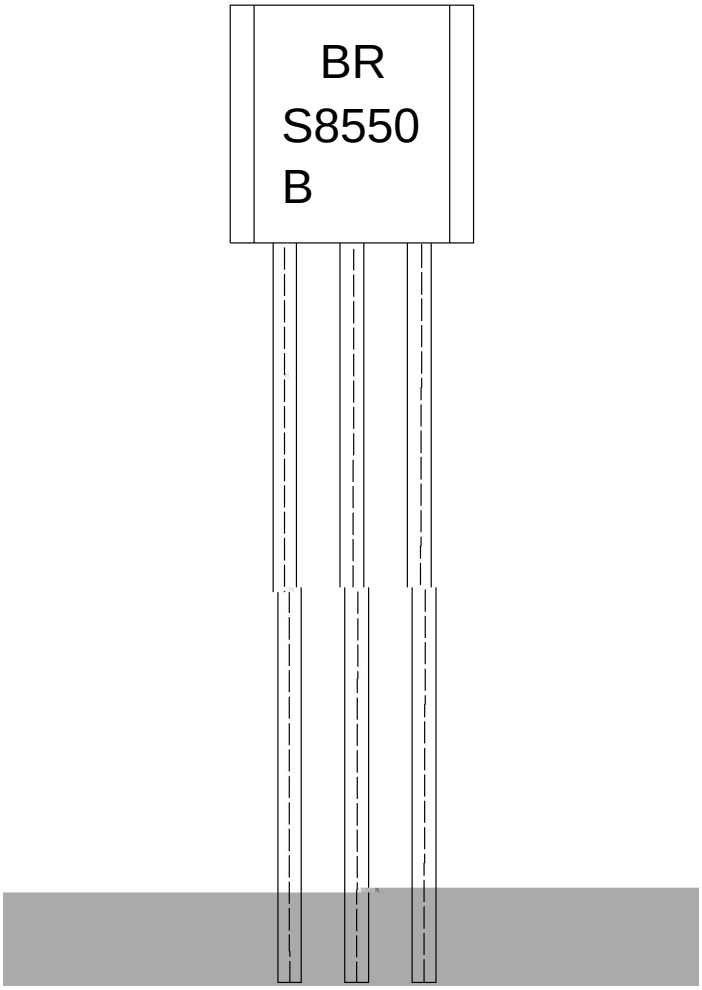




/ Package Dimensions



/ Marking Instructions



BR

S8550

B: h_{FE}

****

Note:

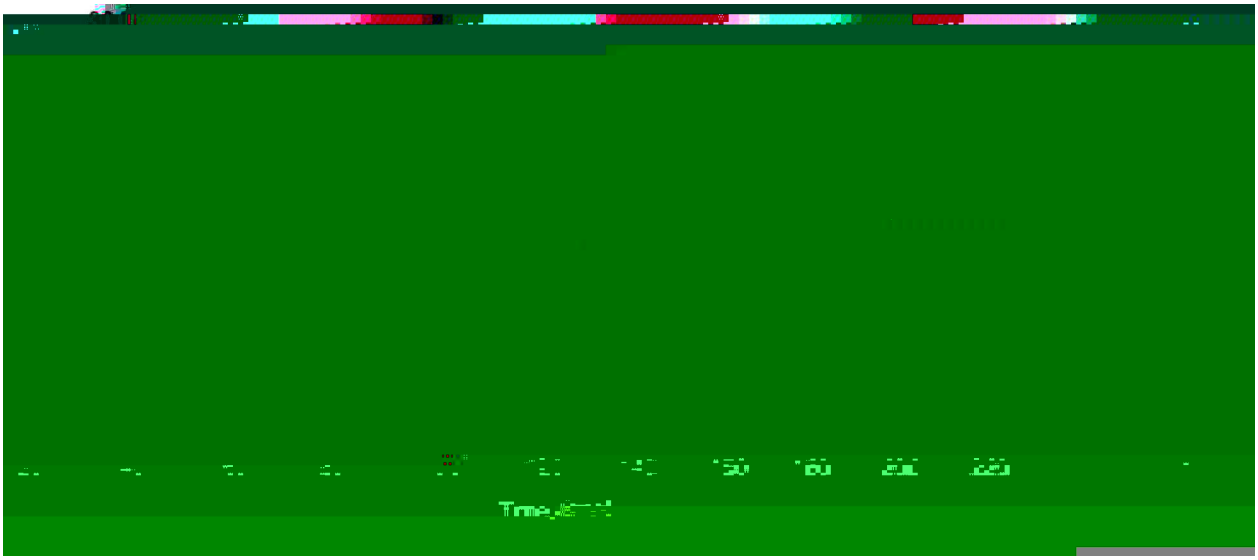
BR: Company Code.

S8550: Product Type.

B: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5		10±1 sec.		Tf0.56Db2f֒j/TT2	1	Tf2	0	TD-0.0005;